

BIPOLAR ANALOG INTEGRATED CIRCUIT

μ PC3228T5S

LOW DISTORTION DOWN-CONVERTER + AGC AMPLIFIER + VIDEO AMPLIFIER

DESCRIPTION

The μ PC3228T5S is a silicon bipolar monolithic IC designed for use as IF down-converter for digital TV, digital CATV. This IC consists of AGC amplifier, mixer and video amplifier.

The package is 32-pin plastic QFN (Quad Flat Non-lead) package suitable for surface mount.

This IC is manufactured using our 30 GHz fmax UHS0 (Ultra High Speed Process) silicon bipolar process.

This process uses silicon nitride passivation film. This material can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformly and reliability.

FEATURES

Total performance : Icc = 85 mA TYP. @ Vcc = 5 V

• AGC AMPLIFIER + MIXER + DRIVER BLOCK : fre (BW) = 20 to 800 MHz

: CG = 28 dB TYP. : GCR = 70 dB TYP.

: $IM_3 = 47$ dBc MIN./57 dBc TYP. @ Single Ended-OUT = 0.5 V_{p-p} /tone

VIDEO AMPLIFIER BLOCK : Gv = 59 dB TYP.

: $f_{IF}(BW) = 20 \text{ to } 100 \text{ MHz}$

: IM₃ = 45 dBc MIN./55 dBc TYP. @ Output = 110 dBu/tone, Differential-out

• High-density surface mounting : 32-pin plastic QFN package ($5.0 \times 5.0 \times 0.75$ mm)

APPLICATION

- Digital CATV
- · Cable modem receivers

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC3228T5S-E2	μPC3228T5S-E2-A	32-pin plastic QFN (Pb-Free)	C3228	 Embossed tape 12 mm wide Pin 8,9 face the perforation side of the tape Qty 2.5 kpcs/reel Dry pack specification

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: μ PC3228T5S

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Document No. PU10623EJ01V0DS (1st edition) Date Published June 2006 NS CP(K)

INTERNAL BLOCK DIAGRAM AND PIN CONFIGURATION

(Top View) 24 GND-AGC GND-AGC Note GND-MIX RF_AGC AMP GND-Driv LO-IN2 Driv-OUT1 27 LO-IN1 LO AMP Driv-OUT2 28 **GND-LO** Driver AMP GND-Driv 29 Vcc-IF2 AGC Control GND IF-OUT2 IF_IN AMP2 IF_IN AMP 10 IF-IN1 IF-OUT1 Driver AMP IF-IN2 GND-IF2 Note Vcc-IF1 VAGC GND-REG S GND-REG GND-IF1 GND-IF2

Note 1, 9, 17, 25-pin: Connected to the lead frame.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25°C	6.0	V
Power Dissipation	PD	$T_A = +80^{\circ}C$ Note	800	mW
Operating Ambient Temperature	TA	Note	-20 to +80	°C
Storage Temperature	Tstg		-55 to +150	°C

Note Mounted on double-sided copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB

RECOMMENDED OPERATING RANGE (Ta = +25°C, unless otherwise specified)

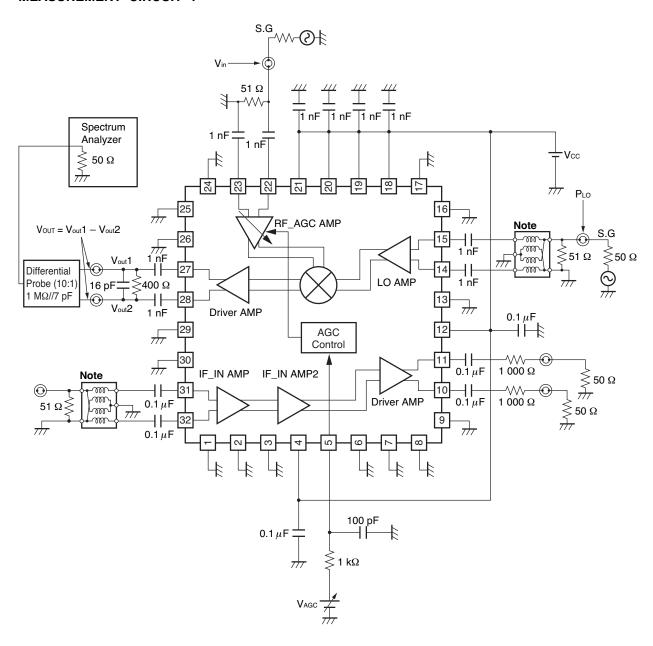
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc		4.5	5.0	5.5	٧
Operating Ambient Temperature	TA	Vcc = 4.5 to 5.5 V	-20	+25	+80	°C
Gain Control Voltage Range	VAGC		0	-	3.3	٧
RF Operating Frequency Range	frf (BW)		20	-	800	MHz
IF Operating Frequency Range	fiF (BW)		20	-	100	MHz

ELECTRICAL CHARACTERISTICS (Ta = +25°C, Vcc = 5 V, unless otherwise specified)

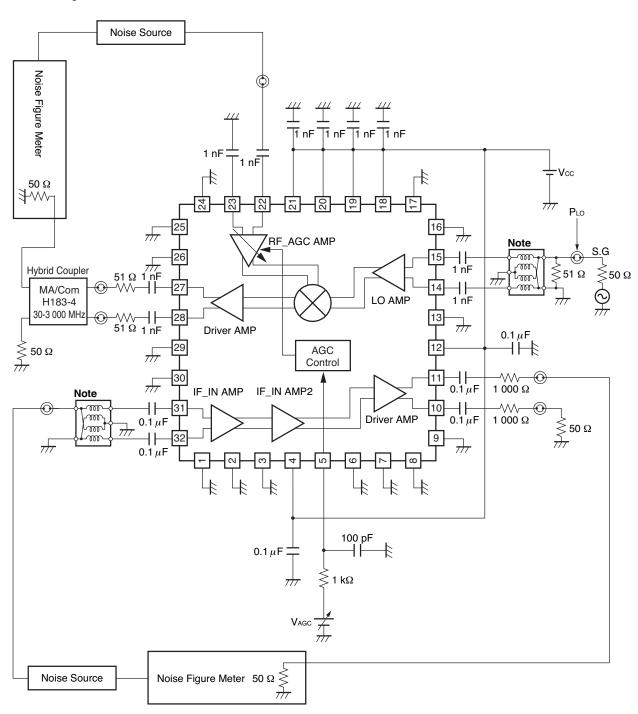
Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
DC Characteristics							
Circuit Current	Icc	No input signal	Note 1	65	85	110	mA
AGC Voltage High Level	VAGC (H)	@ Maximum gain	Note 1	2.5	-	3.5	٧
AGC Voltage Low Level	VAGC (L)	@ Minimum gain	Note 1	-	0	-	V
RF Characteristics (RF AGC Amplifier Block + Mixer Block	+ Driver An	nplifier: fr= 80 MHz, flo = 130 N	1Hz, Plo =	: –10 dBm,	Zs = 50 Ω,	ZL = 400 S	Ω/16 pF)
RF Input Frequency Range	f _{RF}	fc = -3 dB	Note 1	20	-	800	MHz
RF Gain Control Range	GCR1	V _{AGC} = 0 to 2.5 V	Note 1	62	70	-	dB
Mixer Conversion Gain	CG	Vagc = 2.5 V Differential-IN: Vin = +18 dBmV	Note 1	25	28	31	dB
3rd Order Intermodulaion Distortion	IM₃1	f1 = 44 MHz, f2 = 45 MHz, V_{in} = +30 dBmV/tone, Single Ended-OUT = 0.5 V_{p-p}/t	one Note 1	47	57	-	dBc
Noise Figure	NF1	V _{AGC} = 2.5 V, f = 50 MHz, Differential-Output	Note 2	-	8.3	-	dB
IF Characteristics (IF Amplifier Block + Driver Amplifier: fir:	= 50 MHz,	Zs = 50 Ω, ZL = 2 100 Ω)					
IF Input Frequency Range	fıF	fc = -3 dB	Note 5	20	-	100	MHz
IF Amplifier Gain	G∨	V _{in} = -7 dBmV, Differential-IN/OUT	Note 5	56	59	62	dB
3rd Order Intermodulaion Distortion	IM₃2	f1 = 49.5 MHz, f2 = 50.5 MHz, V_{out} = 110 dBu/tone, Differential-IN/OUT	Note 5	45	55	-	dBc
IF Output Voltage	Vout	Single Ended-Output	Note 5	-	1.0	-	V _{p-p}
Noise Figure	NF2	V _{AGC} = 0 V, f = 50 MHz, Single Ended-Output	Note 2	-	3.0	-	dB
Total Block (RF AGC Amplifier + Mixer SAW Filter : EPCOS X6889M (fi= 49		•		•	,.		
LO-RF Leakage	LORF	V_{AGC} = 2.5 V, 22-pin 75 Ω Term fLo = 110 to 180 MHz	mination Note 3	-	-54	-44	dBmV
LO-IF Leakage	LOif	$V_{AGC} = 2.5 \text{ V},$ $V_{out} = 0.7 \text{ V}_{P-P} \text{ Single Ended-O}$ $f_{RF} = 130 \text{ MHz}, f_{LO} = 179 \text{ MHz}$		-	-40	-25	dBc

Notes 1. By measurement circuit 1

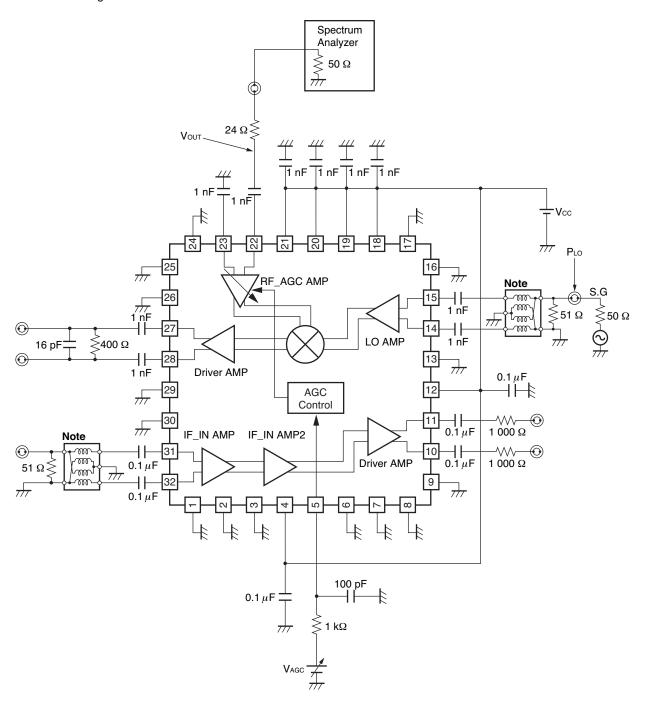
- 2. By measurement circuit 2
- 3. By measurement circuit 3
- 4. By measurement circuit 4
- 5. By measurement circuit 5



Noise Figure

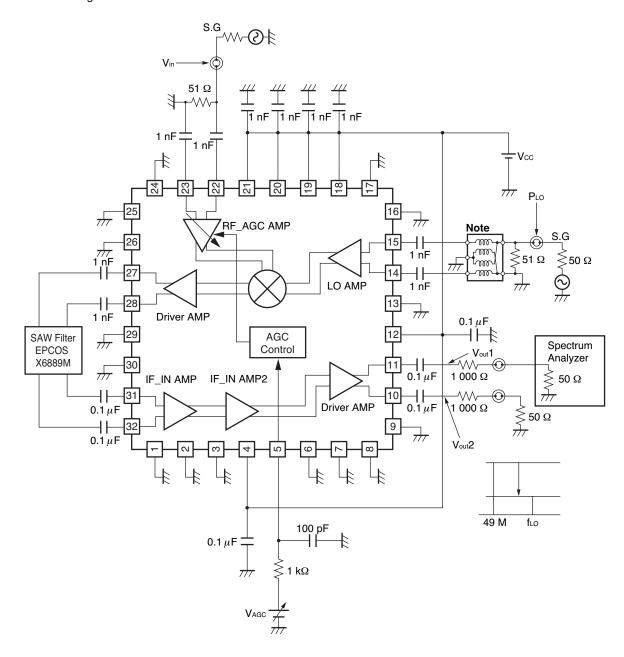


Lo-RF Leakage



(fre = 70 to 130 MHz (fre = 49.1 MHz \pm 0.6 MHz), fLo = 119 to 179 MHz, PLo = -10 dBm, Vout = 0.7 Vp-p (Single Ended))

LO-IF Leakage



IF Block

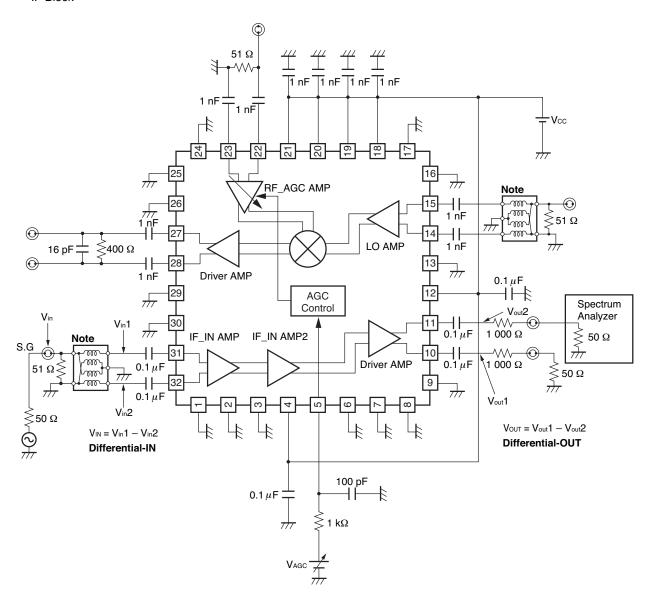
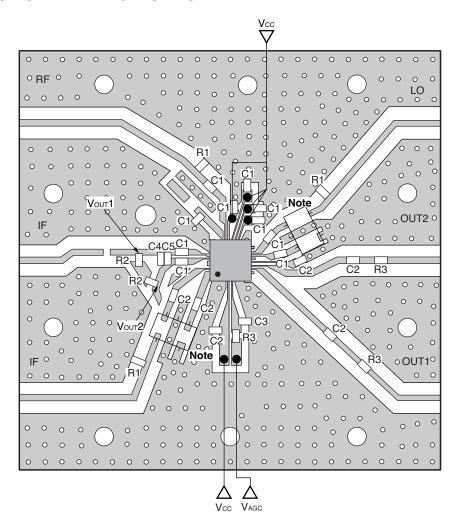


ILLUSTRATION OF THE EVALUATION BOARD



Note Balun Transformer: TOKO 617DB-1674 B4F (Double balanced type)

Remarks

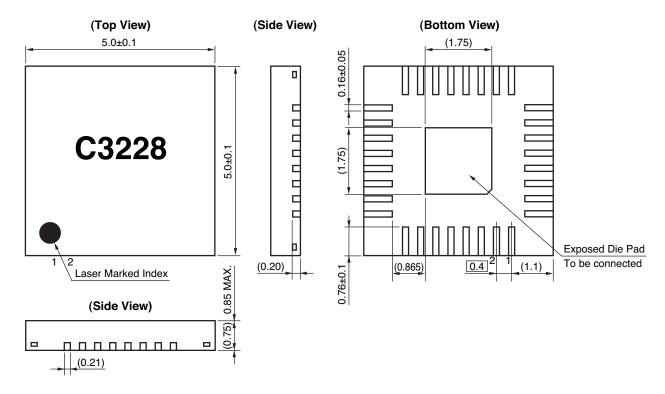
Back side: GND pattern
 Solder plated on pattern
 O: Through hole

USING THE NEC EVALUATION BOARD

Symbol	Values	Maker	Part Number	Size
C1	1 nF	Murata	GRM39CH	1608
C2	0.1 μF	Murata	GRM39B	1608
C3	100 pF	Murata	GRM39CH	1608
C4	10 pF	Murata	GRM36B	1005
C5	6 pF	Murata	GRM36B	1005
R1	51 Ω	Susumu	RR0816 510SSM	1608
R2	200 Ω	Susumu	RR0816 201SSM	1608
R3	1 000 Ω	Susumu	RR0816 102SSM	1608

PACKAGE DIMENSIONS

32-PIN PLASTIC QFN (UNIT: mm)



NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground terminals must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	ethod Soldering Conditions			
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260	
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260	
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350	

Caution Do not use different soldering methods together (except for partial heating).



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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The -AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration in CEL	on contained devices	
Lead (Pb)	< 1000 PPM	-A -AZ Not Detected (*)		
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
PBB	< 1000 PPM	Not De	etected	
PBDE	< 1000 PPM	Not Detected		

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

Important Information and Disclaimer: Information provided by CEL on its website or in other communications concerting the substance content of its products represents knowledge and belief as of the date that it is provided. CEL bases its knowledge and belief on information provided by third parties and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. CEL has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. CEL and CEL suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

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